Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-9. (Canceled)

10. (Currently amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

setting said substrate onto a stage having a plurality of suction inlets;

flattening said substrate by vacuum-sucking a lower surface of said substrate by said plurality of suction inlets; and

irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction and which has a length of 10 cm or more while relatively moving said substrate perpendicular to the one direction ~~with respect to said laser beam~~, and while vacuum-sucking said lower surface of said substrate.

11. (Previously presented) A method according to claim 10 wherein said laser beam is an excimer laser beam.

12. (Previously presented) A method according to claim 10 wherein said semiconductor device is a liquid crystal display device.

13-15. (Canceled)

16. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

heating said semiconductor film;

setting said substrate onto a stage having a plurality of suction inlets;

flattening said substrate by vacuum-sucking a lower surface of said substrate by said plurality of suction inlets; and

irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction and which has a length of 10 cm or more while relatively moving said substrate perpendicular to the one direction ~~with respect to said laser beam~~, and while vacuum-sucking said lower surface of said substrate.

17. (Previously presented) A method according to claim 16 wherein said laser beam is an excimer laser beam.

18. (Previously presented) A method according to claim 16 wherein said semiconductor device is a liquid crystal display device.

19-21. (Canceled)

22. (Currently Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

heating said substrate to crystallize said semiconductor film;

setting said substrate onto a stage having a plurality of suction inlets;

flattening said substrate by vacuum-sucking a lower surface of said substrate by said plurality of suction inlets; and

irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction and which has a length of 10 cm or more while relatively moving said substrate perpendicular to the one direction ~~with respect to said laser beam~~, and while vacuum-sucking said lower surface of said substrate.

23. (Previously presented) A method according to claim 22 wherein said laser beam is an excimer laser beam.

24. (Previously presented) A method according to claim 22 wherein said semiconductor device is a liquid crystal display device.

25. (Previously presented) A method of manufacturing a liquid crystal display device comprising the steps of:

forming a semiconductor film over a substrate having an insulating surface;

heating said substrate and said semiconductor film, wherein said heating deforms said substrate and said semiconductor film from flat to curved;

flattening said substrate by cooling; and

irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam.

26. (Previously presented) A method according to claim 25 wherein said laser beam is an excimer laser beam.

27. (Previously presented) A method according to claim 25 wherein at least a part of the flattened substrate constitutes the liquid crystal display device.

28. (Previously presented) A method of manufacturing a liquid crystal display device comprising the steps of:

forming a semiconductor film over a substrate having an insulating surface;

heating said substrate to crystallize said semiconductor, wherein said heating deforms said substrate and said semiconductor film from flat to curved;

flattening said substrate by cooling; and

irradiating the crystallized semiconductor film with a laser beam.

29. (Previously presented) A method according to claim 28 wherein said laser beam is an excimer laser beam.

30. (Previously presented) A method according to claim 28 wherein at least a part of the flattened substrate constitutes the liquid crystal display device.

31-37. (Canceled)

38. (Previously presented) A method according to claim 10 wherein said substrate is a glass substrate.

39. (Canceled)

40. (Previously presented) A method according to claim 16 wherein said substrate is a glass substrate.

41. (Canceled)

42. (Previously presented) A method according to claim 22 wherein said substrate is a glass substrate.

43. (Previously presented) A method according to claim 25 wherein said substrate is a glass substrate.

44. (Previously presented) A method according to claim 28 wherein said substrate is a glass substrate.

45. (Canceled)

46. (Previously presented) A method according to claim 10 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

47. (Canceled)

48. (Previously presented) A method according to claim 16 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

49. (Canceled)

50. (Previously presented) A method according to claim 22 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

51. (Previously presented) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

setting said substrate onto a stage having a plurality of suction inlets;

flattening said substrate by vacuum-sucking a lower surface of said substrate by said plurality of suction inlets; and

irradiating said semiconductor film with a laser beam while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

52. (Previously presented) A method according to claim 51 wherein said laser beam is an excimer laser beam.

53. (Previously presented) A method according to claim 51 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

54. (Previously presented) A method according to claim 51 wherein said substrate is a glass substrate.

55. (Previously presented) A method according to claim 51 wherein said semiconductor device is a liquid crystal display device.

56. (Previously presented) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

heating said semiconductor film;

setting said substrate onto a stage having a plurality of suction inlets;

flattening said substrate by vacuum-sucking a lower surface of said substrate by said plurality of suction inlets; and

irradiating said semiconductor film with a laser beam while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

57. (Previously presented) A method according to claim 56 wherein said laser beam is an excimer laser beam.

58. (Previously presented) A method according to claim 56 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

59. (Previously presented) A method according to claim 56 wherein said substrate is a glass substrate.

60. (Previously presented) A method according to claim 56 wherein said semiconductor device is a liquid crystal display device.

61. (Canceled)

62. (Previously presented) A method according to claim 10 wherein said stage has a surface roughness of 5 □m or less.

63. (Canceled)

64. (Previously presented) A method according to claim 16 wherein said stage has a surface roughness of 5 μm or less.

65. (Canceled)

66. (Previously presented) A method according to claim 22 wherein said stage has a surface roughness of 5 μm or less.

67. (Previously presented) A method according to claim 51 wherein said stage has a surface roughness of 5 μm or less.

68. (Previously presented) A method according to claim 56 wherein said stage has a surface roughness of 5 μm or less.

69. (Previously presented) A method according to claim 10 further comprising a step of fixing said substrate by a pusher after setting said substrate onto said stage.

70. (Previously presented) A method according to claim 16 further comprising a step of fixing said substrate by a pusher after setting said substrate onto said stage.

71. (Previously presented) A method according to claim 22 further comprising a step of fixing said substrate by a pusher after setting said substrate onto said stage.

72. (Previously presented) A method according to claim 51 further comprising a step of fixing said substrate by a pusher after setting said substrate onto said stage.

73. (Previously presented) A method according to claim 56 further comprising a step of fixing said substrate by a pusher after setting said substrate onto said stage.

74. (New) A method according to claim 10, wherein said length of said laser beam is 30 cm or less.

75. (New) A method according to claim 16, wherein said length of said laser beam is 30 cm or less.

76. (New) A method according to claim 22, wherein said length of said laser beam is 30 cm or less.

77. (New) A method according to claim 10, wherein a difference in level of the surface of the flattened substrate is a focal depth of the laser beam or less.

78. (New) A method according to claim 16, wherein a difference in level of the surface of the flattened substrate is a focal depth of the laser beam or less.

79. (New) A method according to claim 22, wherein a difference in level of the surface of the flattened substrate is a focal depth of the laser beam or less.

80. (New) A method according to claim 25, wherein a difference in level of the surface of the flattened substrate is a focal depth of the laser beam or less.

81. (New) A method according to claim 28, wherein a difference in level of the surface of the flattened substrate is a focal depth of the laser beam or less.

82. (New) A method according to claim 51, wherein a difference in level of the surface of the flattened substrate is a focal depth of the laser beam or less.

83. (New) A method according to claim 56, wherein a difference in level of the surface of the flattened substrate is a focal depth of the laser beam or less.

84. (New) A method according to claim 10, wherein a roughness and waviness of the surface of the flattened substrate are each 5 □m or less.

85. (New) A method according to claim 16, wherein a roughness and waviness of the surface of the flattened substrate are each 5 □m or less.

86. (New) A method according to claim 22, wherein a roughness and waviness of the surface of the flattened substrate are each 5 □m or less.

87. (New) A method according to claim 25, wherein a roughness and waviness of the surface of the flattened substrate are each 5 □m or less.

88. (New) A method according to claim 28, wherein a roughness and waviness of the surface of the flattened substrate are each 5 □m or less.

89. (New) A method according to claim 51, wherein a roughness and waviness of the surface of the flattened substrate are each 5 □m or less.

90. (New) A method according to claim 56, wherein a roughness and waviness of the surface of the flattened substrate are each 5 □m or less.